

L Number	Hits	Search Text	DB	Time stamp
1	2908855	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:22
2	19603	(memory or storage) and (ferroelectric or ferro-electric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:23
3	343	((memory or storage) and (ferroelectric or ferro-electric)) and transistor with capacitor with parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:24
4	59	(((memory or storage) and (ferroelectric or ferro-electric)) and transistor with capacitor with parallel) and column adj2 decoder	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:25

L Number	Hits	Search Text	DB	Time stamp
1	2908855	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 10:06
2	19603	(memory or storage) and (ferroelectric or ferro-electric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 10:07
3	343	((memory or storage) and (ferroelectric or ferro-electric)) and capacitor with transistor with parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 10:08
5	166	((((memory or storage) and (ferroelectric or ferro-electric)) and capacitor with transistor with parallel) and plate adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 10:31
7	15	(((memory or storage) and (ferroelectric or ferro-electric)) and capacitor with transistor with parallel) and plate adj line) and plate adj line adj driver and column adj3 decoder	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 10:32